L Number	Hits	Search Text	DB	Time stamp
1	5617		USPAT;	2004/10/18 07:33
_	301,	layer and pn same layer	US-PGPUB;	
			EPO;	
			DERWENT	
2	2030	semiconductor same device and diffusion and	USPAT;	2004/10/18 07:33
		layer and pn same layer and chip	US-PGPUB;	
			EPO;	
			DERWENT	
3	608	semiconductor same device and diffusion and	USPAT;	2004/10/18 08:44
		layer and pn same layer and single same chip	US-PGPUB;	
			EPO; DERWENT	
4	2	semiconductor same device and diffusion and	USPAT;	2004/10/18 08:33
•	_	layer and pn same layer and single same chip	US-PGPUB;	2004/10/10 00:33
		and analytic same circuit	EPO;	
		•	DERWENT	
5	55710	Takashi	USPAT;	2004/10/18 08:33
			US-PGPUB;	
			EPO;	
_	:		DERWENT	
6	55		USPAT;	2004/10/18 08:50
		layer and pn same layer and a same ray and	US-PGPUB;	
		single same chip	EPO;	
8	34	semiconductor same device and diffusion and	DERWENT	2004/10/18 08:57
0	34	layer and pn same layer and detect same ray	USPAT; US-PGPUB;	2004/10/16 08:5/
		rayer and pir same rayer and detect same ray	EPO;	
			DERWENT	
9	36	semiconductor same device and diffusion and	USPAT;	2004/10/18 09:01
	1	layer and pn same junction and detect same	US-PGPUB;	,,
		ray	EPO;	
	1		DERWENT	
11	36	semiconductor same device and diffusion and	USPAT;	2004/10/18 10:08
		layer and pn same junction and detect same	US-PGPUB;	
		ray	EPO;	
12	1055866	semigordugtor diffusion and lawer and Unn	DERWENT	2004/10/18 00:02
12	1033000	semiconductor diffusion and layer and "pn junction" and detect same ray	USPAT; US-PGPUB;	2004/10/18 09:03
		Juneton and detect same ray	EPO;	
			DERWENT	
13	1055865	semiconductor diffusion and layer and "pn	USPAT;	2004/10/18 09:03
		junction" and detect same alpha same ray	US-PGPUB;	
			EPO;	
			DERWENT	
14	5	semiconductor and diffusion and layer and	USPAT;	2004/10/18 09:16
		"pn junction" and detect same alpha same ray	US-PGPUB;	
			EPO;	
16	3	semiconductor and diffusion and layer and	DERWENT USPAT;	2004/10/18 09:19
10	,	"pn junction" and detect same alpha same ray	US-PGPUB;	2004/10/18 09:19
		and electric same charge	EPO;	
		3 -	DERWENT	
17	19	semiconductor and diffusion and "pn	USPAT;	2004/10/18 09:22
		junction" and detect same ray and electric	US-PGPUB;	_
		same charge	EPO;	
, ,			DERWENT	
18	50	p.	USPAT;	2004/10/18 09:24
		junction" and detect same ray	US-PGPUB;	
[EPO; DERWENT	
19	5	semiconductor and diffusion and "pn	USPAT;	2004/10/18 09:41
		junction" and detect same alpha same ray	US-PGPUB;	2004/10/10 03:41
		The same say	EPO;	
			DERWENT	
20	213	257/225.ccls.	USPAT;	2004/10/18 09:47
			US-PGPUB;	
			EPO;	
			DERWENT	

21	547	250/370.01.ccls.	USPAT; US-PGPUB;	2004/10/18 10:04
22	56	250/370.02.ccls.	EPO; DERWENT USPAT; US-PGPUB; EPO;	2004/10/18 09:48
23	1	257/225.ccls. and semiconductor and diffusion and "pn junction" and detect same alpha same ray	DERWENT USPAT; US-PGPUB; EPO;	2004/10/18 10:07
24	1	257/225.ccls. and "pn junction" and detect same alpha same ray	DERWENT USPAT; US-PGPUB; EPO;	2004/10/18 09:47
28	1	250/370.02.ccls. and semiconductor and diffusion and "pn junction" and detect same alpha same ray	DERWENT USPAT; US-PGPUB; EPO;	2004/10/18 09:49
29	3	250/370.02.ccls. and semiconductor and diffusion and pn	DERWENT USPAT; US-PGPUB; EPO;	2004/10/18 09:49
30	1	250/370.05.ccls. and semiconductor and diffusion and "pn junction" and detect same alpha same ray	DERWENT USPAT; US-PGPUB; EPO;	2004/10/18 09:49
38	1		DERWENT USPAT; US-PGPUB; EPO;	2004/10/18 10:00
37	362	250/390.01.ccls.	DERWENT USPAT; US-PGPUB; EPO;	2004/10/18 10:00
39	1	257/225.ccls. and semiconductor and diffusion and alpha same ray	DERWENT USPAT; US-PGPUB; EPO;	2004/10/18 10:04
41	3939	250/370\$	DERWENT USPAT; US-PGPUB; EPO;	2004/10/18 10:05
43	7	250/370\$ and diffusion and layer and alpha adj ray and electric same charge	DERWENT USPAT; US-PGPUB; EPO;	2004/10/18 10:06
44	13	250/370\$ and diffusion and layer and alpha adj ray	DERWENT USPAT; US-PGPUB; EPO;	2004/10/18 10:06
46	213	257/225.ccls.	DERWENT USPAT; US-PGPUB; EPO;	2004/10/18 10:07
~	8189226	JP "10260135"	DERWENT USPAT; US-PGPUB; EPO;	2004/10/15 10:20
-	8189224	JP "10260135" and Mitsubishi	DERWENT USPAT; US-PGPUB; EPO;	2004/10/15 10:21
-	79	250/370.05.ccls.	DERWENT USPAT; US-PGPUB; EPO;	2004/10/18 09:49
-	1	250/370.05.ccls. and diffusion same layer and isotope	DERWENT USPAT; US-PGPUB; EPO;	2004/10/15 15:30
			EPO; DERWENT	

-	1	250/390.01.ccls. and diffusion same layer	USPAT;	2004/10/18 09:59
		and isotope	US-PGPUB;	
			EPO;	
			DERWENT	
-	223	semiconductor same device and diffusion same	USPAT;	2004/10/15 15:31
	ŀ	layer and isotope	US-PGPUB;	
			EPO;	
			DERWENT	
-	44	semiconductor same device and diffusion same	USPAT;	2004/10/15 15:33
		layer and isotope and a same ray	US-PGPUB;	
			EPO;	
	_		DERWENT	
-	9	radiation and neutron and semiconductor same	USPAT;	2004/10/15 15:34
		device and diffusion same layer and isotope	US-PGPUB;	
		and a same ray	EPO;	
L			DERWENT	